MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MC54/74HC125
MC54/74HC126

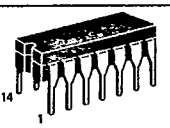
Quad 3-State Noninverting Buffers

High-Performance Silicon-Gate CMOS

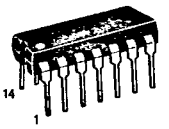
The MC54/74HC125 and MC54/74HC126 are identical in pinout to the LS125 and LS126. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC125 and HC126 noninverting buffers are designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The devices have four separate output enables that are active-low (HC125) or active-high (HC126).

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 72 FETs or 18 Equivalent Gates



J SUFFIX
CERAMIC
CASE 632-08



N SUFFIX
PLASTIC
CASE 646-06

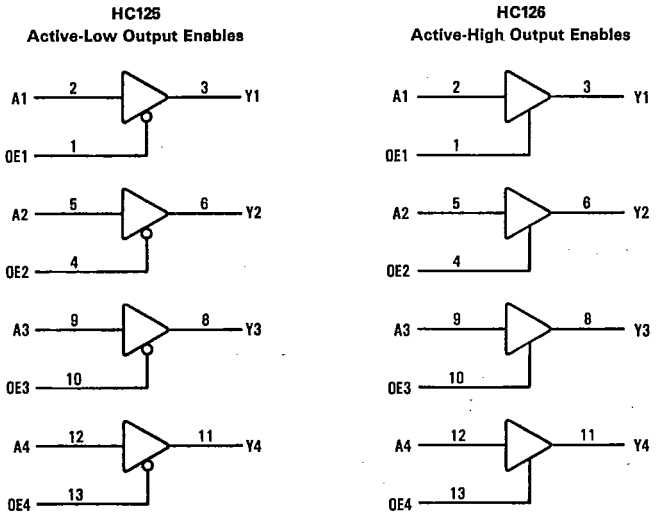
D SUFFIX
SOIC
CASE 751A-02

ORDERING INFORMATION

MC74HCXXXN	Plastic
MC54HCXXXJ	Ceramic
MC74HCXXXD	SOIC

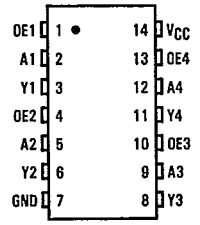
$T_A = -55°$ to 125°C for all packages.
Dimensions in Chapter 7.

LOGIC DIAGRAM



PIN 14 = V_{CC}
PIN 7 = GND

PIN ASSIGNMENT



FUNCTION TABLE

HC125			HC126		
Inputs		Output	Inputs		Output
A	OE	Y	A	OE	Y
H	L	H	H	H	H
L	L	L	L	H	L
X	H	Z	X	L	Z

X = don't care
Z = high impedance

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MC54/74HC125•MC54/74HC126

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	−0.5 to +7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	−1.5 to V_{CC}+1.5	V
V_{out}	DC Output Voltage (Referenced to GND)	−0.5 to V_{CC}+0.5	V
I_{in}	DC Input Current, per Pin	±20	mA
I_{out}	DC Output Current, per Pin	±35	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	±75	mA
P_D	Power Dissipation in Still Air, Plastic or Ceramic DIP†	750	mW
	SOIC Package†	500	
T_{stg}	Storage Temperature	−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		°C
	(Plastic DIP or SOIC Package)	260	
	(Ceramic DIP)	300	

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

*Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — Plastic DIP: −10 mW/°C from 65° to 125°C
Ceramic DIP: −10 mW/°C from 100° to 125°C
SOIC Package: −7 mW/°C from 65° to 125°C
For high frequency or heavy load considerations, see Chapter 4.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)		0	V_{CC}	V
T_A	Operating Temperature, All Package Types		−55	+125	°C
t_r, t_f	Input Rise and Fall Time	V_{CC} = 2.0 V	0	1000	ns
	(Figure 1)	V_{CC} = 4.5 V	0	500	
		V_{CC} = 6.0 V	0	400	

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				25°C to −55°C	≤85°C	≤125°C	
V_{IH}	Minimum High-Level Input Voltage	V_{out} = V_{CC} − 0.1 V, $\|I_{out}\|$ ≤ 20 μA	2.0	1.5	1.5	1.5	V
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
V_{IL}	Maximum Low-Level Input Voltage	V_{out} = 0.1 V, $\|I_{out}\|$ ≤ 20 μA	2.0	0.3	0.3	0.3	V
			4.5	0.9	0.9	0.9	
			6.0	1.2	1.2	1.2	
V_{OH}	Minimum High-Level Output Voltage	V_{in} = V_{IH}, $\|I_{out}\|$ ≤ 20 μA	2.0	1.9	1.9	1.9	V
			4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
		V_{in} = V_{IH}, $\|I_{out}\|$ ≤ 6.0 mA	4.5	3.98	3.84	3.70	
		$\|I_{out}\|$ ≤ 7.8 mA	6.0	5.48	5.34	5.20	
V_{OL}	Maximum Low-Level Output Voltage	V_{in} = V_{IL}, $\|I_{out}\|$ ≤ 20 μA	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
		V_{in} = V_{IL}, $\|I_{out}\|$ ≤ 6.0 mA	4.5	0.26	0.33	0.40	
		$\|I_{out}\|$ ≤ 7.8 mA	6.0	0.26	0.33	0.40	
I_{in}	Maximum Input Leakage Current	V_{in} = V_{CC} or GND	6.0	±0.1	±1.0	±1.0	μA
I_{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State, V_{in} = V_{IL} or V_{IH}, V_{out} = V_{CC} or GND	6.0	±0.5	±5.0	±10.0	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	V_{in} = V_{CC} or GND, I_{out} = 0 μA	6.0	8	80	160	μA

NOTE: Information on typical parametric values can be found in Chapter 4.

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MC54/74HC125•MC54/74HC126

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input $t_r = t_f$ = 6 ns)

Symbol	Parameter	V_{CC} V	Guaranteed Limit			Unit
			25°C to −55°C	≤85°C	≤125°C	
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 3)	2.0 4.5 6.0	100 20 17	125 25 21	150 30 26	ns
t_{PLZ}, t_{PHZ}	Maximum Propagation Delay, Output Enable to Y (Figures 2 and 4)	2.0 4.5 6.0	125 25 21	155 31 26	190 38 32	ns
t_{PZL}, t_{PZH}	Maximum Propagation Delay, Output Enable to Y (Figures 2 and 4)	2.0 4.5 6.0	125 25 21	155 31 26	190 38 32	ns
t_{TLH}, t_{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0 4.5 6.0	60 12 10	75 15 13	90 18 15	ns
C_{in}	Maximum Input Capacitance	—	10	10	10	pF
C_{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)	—	15	15	15	pF

NOTES:
1. For propagation delays with loads other than 50 pF, see Chapter 4.
2. Information on typical parametric values can be found in Chapter 4.

C_{PD}	Power Dissipation Capacitance (Per Buffer) Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ For load considerations, see Chapter 4.	Typical @ 25°C, V_{CC} = 5.0 V 45	pF

SWITCHING WAVEFORMS

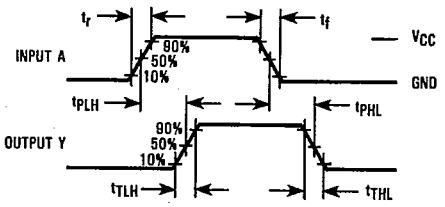


Figure 1

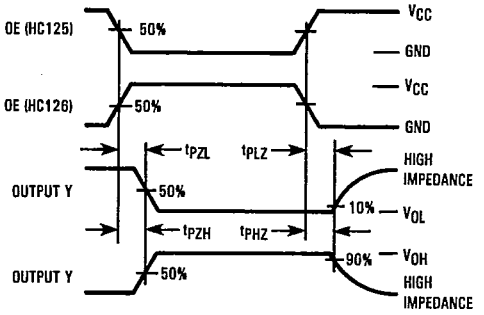
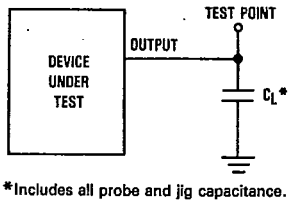
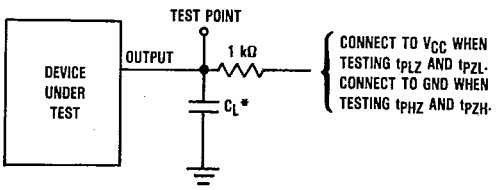


Figure 2



*Includes all probe and jig capacitance.

Figure 3. Test Circuit



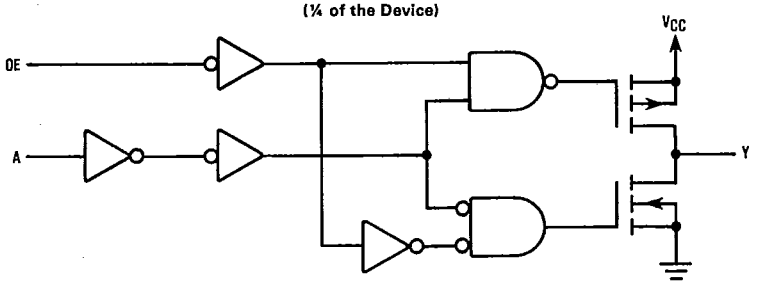
*Includes all probe and jig capacitance.

Figure 4. Test Circuit

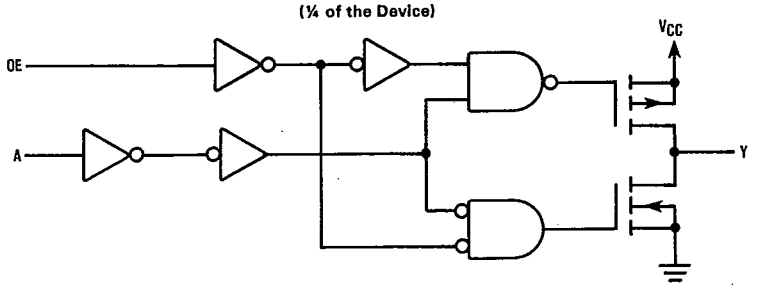
MC54/74HC125•MC54/74HC126

LOGIC DETAILS

HC125
(¼ of the Device)



HC126
(¼ of the Device)



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